Prof. Ohmi's Paper

January – December, 2008

E1290 (F) ICHIROU TAKAHASHI, MASAKI HIRAYAMA, YASUYUKI SHIRAI, AKINOBU TERAMOTO, SHIGETOSHI SUGAWA and TADAHIRO OHMI, “13.56 and 100 MHz Coupled Mode Rf-Sputtering for Ferroelectric Sr$_2$(Ta$_{1-x}$,Nb$_x$)O$_7$ (STN) Film Applied to One-Transistor Type Ferroelectric Random Access Memory,” Ferroelectrics, Vol.368, pp.90-95, January 2008.


E1307(C) P. Gaubert, A. Teramoto, W. Cheng, T. Hamada, and T. Ohmi, “Different mechanism to explain the 1/f noise in n-and p-SOI-MOS transistors fabricated on (110) and (100) silicon oriented wafers,” 15th Workshop on Dielectrics in Microelectronics, pp151-152, Berlin, June 2008.


